IN THE SPECIFICATION:

Replace the paragraph beginning at page 1, line 23 with:

C1

A phenomenon in which an electrostatically charged object contacts ~~with~~ other object(s) and causes an electrical discharge is called ESD (Electro Static Discharge). ~~The~~ When this phenomenon ~~happened at~~ happens to a semiconductor device, it may destroy semiconductor elements of the semiconductor device. As ~~theoretic~~ theoretical models of ESD, ~~discharge models of~~ the HBM (Human Body Model) ~~presenting~~ represents a discharge from an electrically charged human body to semiconductor elements, MM (Machine Model) ~~presenting~~ represents a discharge from an electrically charged machine to a semiconductor element, and CDM (Charge Device Model) ~~presenting~~ represents a discharge from a charged semiconductor device itself to a grounded object ~~are well known~~. The current waveforms of HBM and CDM are shown in FIG. 1. In the figure, a current of approximately 1 A ~~is caused~~ flows for a relatively long time (up to 100 ns) in the HBM and ~~on the other hand,~~ a large current of approximately 10 A ~~is caused~~ flows for a very short time (up to 1 ns) in the CDM.

Replace the paragraph beginning at page 2, line 22 with:

C2

In order to prevent ~~these~~ such destruction, various protection circuits are typically ~~formed into the~~ included in a semiconductor device between internal ~~circuit~~ circuits on a Si wafer and I/O pins so ~~as not to transmit~~ a high voltage surge due to EDS is not transmitted to the internal circuit. Since the I/O pins are connected to I/O pads on the wafer through wire bonding, protection circuits are typically ~~formed~~ located between the internal circuit and the I/O pads. Anyway, these protection circuits are commonly used and called as ESD protection circuits.